

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 250 V
- Complementary to 2STA2121
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Application

■ Audio power amplifier

Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

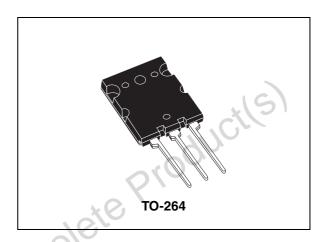


Figure 1. Internal schematic diagram

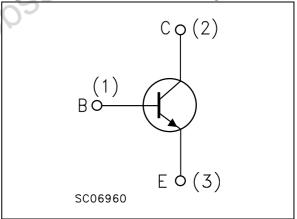


Table 1. Device summary

Order code	Marking	Package	Packaging
2STC5949	2STC5949	TO-264	Tube

Absolute maximum ratings 1

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	250	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	250	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	6	V
I _C	Collector current	17	Α
I _{CM}	Collector peak current (t _P < 5 ms)	34	Α
P _{TOT}	Total dissipation at T _c = 25°C	220	W
T _{stg}	Storage temperature	-65 to 150	Ç
TJ	Max. operating junction temperature	150	°C
Table 3.	Thermal data	2,000	
Symbol	Parameter	Value	Unit

Table 3. Thermal data

S	Symbol	Parameter		Value	Unit
F	R _{thj-case}	Thermal resistance junction-case	max	0.568	°C/W
			0/6		
		Op			
		.(6)			
		AUCIL			
Obsolet	O	oduct(s)			
10,10	S,				
-105010					
Oh					

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 250 V			5	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V			5	μΑ
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA	250		G.	V
V _{(BR)CBO}	Collector-base breakdown voltage (I _F = 0)	I _C = 100 μA	250	40	ر ا	V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA	6)		V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 8 \text{ A}$ $I_B = 800 \text{ mA}$			3	V
V _{BE} ⁽¹⁾	Base-emitter voltage	$I_C = 7 A$ $V_{CE} = 5 V$			1.5	V
h _{FE}	DC current gain	$I_C = 1 A$ $V_{CE} = 5 V$ $I_C = 7 A$ $V_{CE} = 5 V$	80 35		160	
f _T	Transition frequency	I _C = 1 A V _{CE} = 5 V		25		MHz

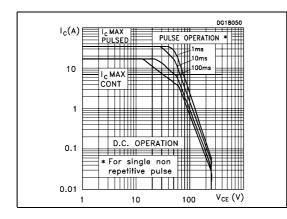
^{1.} Pulsed duration = 300 μs, duty cycle ≤ 1.5%

Electrical characteristics 2STC5949

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



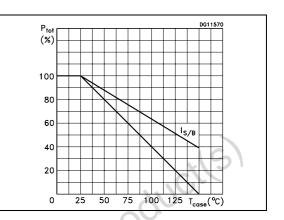
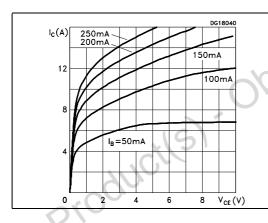


Figure 4. Output characteristics

Figure 5. DC current gain



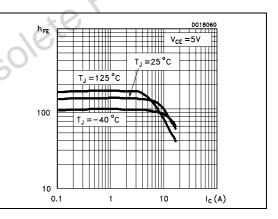
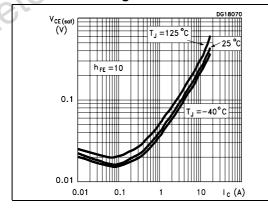
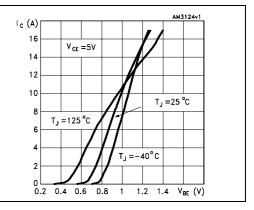


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter voltage





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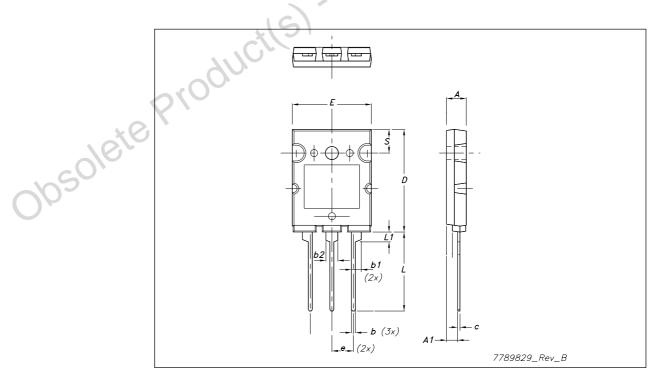
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s). Obsolete Product(s)

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	U-Z	.04	we	CHa	HIIC:a	i uaia

Dim.		mm.		
	Min.	Тур	Max.	
Α	4.80		5.20	
A1	2.50		3.10	
b	0.90	1.0	1.25	
b1		2.5		
b2		2.8	40,	
С	0.50	0.60	0.85	
D	25.6		26.4	
Е	19.80	201	20.20	
е	5.15	10,1	5.75	
L	19.50	c0/	20.50	
L1	2.30	75	2.70	
øΡ	3.55	7	3.65	



2STC5949 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
26-Nov-2007	1	Initial release
05-May-2008	2	New graphics.
11-Jul-2008	3	Updated Figure 7.
17-Nov-2008	4	Content reworked to improve readability, no technical changes

Obsolete Product(s)

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